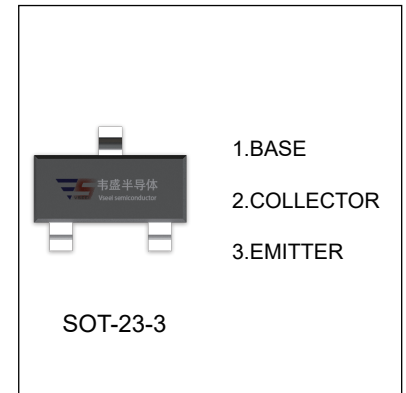


BC808 TRANSISTOR (PNP)

FEATURES

- Suitable for AF-Driver stages and low power output stages
- Complement to BC818



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current –Continuous	-0.8	A
P _{C*}	Collector Power Dissipation	300	mW
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-25V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	100		630	
	h _{FE(2)}	V _{CE} =-1V, I _C =-300mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-0.7	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-300mA			-1.2	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=50MHz		100		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		12		pF

CLASSIFICATION OF h_{FE}

Rank	16	25	40
Range h _{FE(1)}	100-250	160-400	250-630
Marking	5E	5F	5G